



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Schuegraf et al.) Group Art Unit 2811
)
 Appl. No. : 08/932,228)
)
 Filed : September 17, 1997)
)
 For : SHALLOW TRENCH)
 ISOLATION USING LOW)
 DIELECTRIC CONSTANT)
 INSULATOR)
)
 Examiner : H. VU)

#17/P
JHM

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PRELIMINARY AMENDMENT UCI 4 2000
 TECHNOLOGY CENTER 2800

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Prior to examination on the merits in the present continued prosecution application (CPA), please amend the above-captioned application as indicated below.

IN THE CLAIMS:

11. (Twice Amended) An isolation structure in a semiconductor substrate comprising:

a recessed portion formed [therein in] with a vertical sidewall within the semiconductor substrate; and

a dielectric material comprising a halide-doped silicon oxide filling the recessed portion, said dielectric material having a dielectric constant lower than the dielectric constant of silicon dioxide.

Please add the following new claims: